

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Previously Presented) An image-sensing apparatus comprising:
a plurality of pixels, the pixels each comprising:
a photoelectric conversion portion having a photosensitive element and a field effect transistor configured to produce an electric signal in accordance with amount of incident light and that outputs a signal obtained by converting the electric signal natural-logarithmically;
a lead-out path by way of which the signal output from the photoelectric conversion portion is fed to an output signal line; and
a controller that detects a variation in sensitivity of the photoelectric conversion portion of each pixel by causing an electric charge indicative of the threshold voltage of the field effect transistor to accumulate on the field effect transistor and reading out the electric charge via the lead-out path.
2. (Original) An image-sensing apparatus as claimed in claim 1, wherein the pixels are arranged in a matrix.
3. (Canceled)
4. (Withdrawn) An image-sensing apparatus as claimed in claim 3, wherein the pixels each further comprise a resetting portion, and wherein, after each pixel outputs the signal integrated by the integrator circuit to the output signal line, the controller makes the resetting portion discharge an electric charge from the integrator circuit.

5. (Withdrawn) An image-sensing apparatus as claimed in claim 4,
wherein the resetting portion comprises a transistor having a first electrode
connected to the integrator circuit, a second electrode, and a control electrode, and
wherein the controller achieves discharging of the electric charge from the
integrator circuit by varying a voltage applied to the control electrode of the transistor so
that the transistor is brought into a conducting state.

6. (Original) An image-sensing apparatus as claimed in claim 1,
wherein the pixels each further comprise an amplifying transistor that amplifies the
signal output from the photoelectric conversion portion so that a signal output from the
amplifying transistor is fed by way of the lead-out path to the output signal line.

7. (Original) An image-sensing apparatus as claimed in claim 6, further
comprising:
load resistors or constant-current sources connected to the output signal line, a total
number of the load resistors or constant-current sources being smaller than a total number
of the pixels.

8. (Original) An image-sensing apparatus as claimed in claim 7,
wherein the load resistors or constant-current sources each comprise a resistive
transistor having a first electrode connected to the output signal line, a second electrode
connected to a direct-current voltage, and a control electrode connected to a direct-current
voltage.

9. (Withdrawn) An image-sensing apparatus as claimed in claim 8,
wherein the amplifying transistor is an N-channel MOS transistor, and
wherein a direct-current voltage applied to a first electrode of the amplifying
transistor is higher than the direct-current voltage applied to the second electrode of the
resistive transistor.

10. (Previously Presented) An image-sensing apparatus comprising:
a plurality of pixels, the pixels each comprising:

a photoelectric conversion portion that has a photosensitive element for producing an electric signal in accordance with amount of incident light and that outputs a signal obtained by converting the electric signal natural-logarithmically;

a lead-out path by way of which the signal output from the photoelectric conversion portion is fed to an output signal line; and

an amplifying transistor that amplifies the signal output from the photoelectric conversion portion so that a signal output from the amplifying transistor is fed by way of the lead-out path to the output signal line; the amplifying transistor being a P-channel MOS transistor;

load resistors or constant-current sources connected to the output signal line, a total number of the load resistors or constant-current sources being smaller than a total number of the pixels, each load resistor or constant-current source including a resistive transistor having a first electrode connected to the output signal line, a second electrode connected to a direct-current voltage, and a control electrode connected to a direct-current voltage; and

a controller that detects a variation in sensitivity of the photoelectric conversion portion of each pixel by injecting an electric charge into the photoelectric conversion portion,

wherein a direct-current voltage applied to a first electrode of the amplifying transistor is lower than the direct-current voltage applied to the second electrode of the resistive transistor.

11. (Original) An image-sensing apparatus as claimed in claim 1,

wherein the lead-out path includes a switch that selects one after another of the pixels in a predetermined sequence and feeds the signal output from the selected pixel to the output signal line.

12. (Previously Presented) An image-sensing apparatus comprising:
a plurality of pixels, the pixels each comprising:

a photoelectric conversion portion that has a photosensitive element for producing an electric signal in accordance with amount of incident light and that outputs a signal obtained by converting the electric signal natural-logarithmically; each photoelectric conversion portion including:

a first electrode to which a direct-current voltage is applied and a second electrode;

a first transistor having a first electrode connected to the second electrode of the photosensitive element, a second electrode, and a control electrode, the first transistor receiving an output current from the photoelectric element; and

a second transistor having a first electrode to which a direct-current voltage is applied, a second electrode from which an electric signal is output, and a control electrode connected to the first electrode of the first transistor;

a lead-out path by way of which the signal output from the photoelectric conversion portion is fed to an output signal line;

a first switching portion for applying a direct-current voltage to the control electrode of the first transistor; and

a second switching portion provided between the control electrode of the first transistor and the control electrode of the second transistor; and

a controller that detects a variation in sensitivity of the photoelectric conversion portion of each pixel by injecting an electric charge into the photoelectric conversion portion,

wherein the controller detects variations in sensitivity of the individual pixels by turning on the first switching portion and turning off the second switching portion so that a predetermined direct-current voltage is applied to the control electrode of the first transistor and that the control electrodes of the first and second transistors are brought into a cut-off state, and

wherein the controller makes the individual pixels perform image sensing by turning off the first switching portion and turning on the second switching portion so that the control electrodes of the first and second transistors are brought into a connected state.

13. (Original) An image-sensing apparatus as claimed in claim 12,
wherein the first switching portion is a third transistor having a first electrode connected to the control electrode of the first transistor, a second electrode to which a direct-current voltage is applied, and a control electrode,
wherein the second switching portion is a fourth transistor having a first electrode connected to the control electrode of the first transistor, a second electrode connected to the control electrode of the second transistor, and a control electrode,
wherein the controller detects variations in sensitivity of the individual pixels by feeding a signal to the control electrode of the third transistor so as to turn on the third transistor and turning off the fourth transistor so that a predetermined direct-current voltage is applied to the control electrode of the first transistor and that the control electrodes of the first and second transistors are brought into a cut-off state, and
wherein the controller makes the individual pixels perform image sensing by turning off the third transistor and feeding a signal to the control electrode of the fourth transistor so as to turn on the fourth transistor so that the control electrodes of the first and second transistors are brought into a connected state.

14. (Original) An image-sensing apparatus as claimed in claim 1,
wherein, during image sensing, the pixels can each operate selectively either in a first state in which the photoelectric conversion portion converts the electric signal linearly and in a second state in which the photoelectric conversion portion converts the electric signal natural logarithmically.

15. (Original) An image-sensing apparatus as claimed in claim 12,
wherein, during image sensing, the pixels can each operate selectively either in a first state in which the photoelectric conversion portion converts the electric signal linearly and in a second state in which the photoelectric conversion portion converts the electric signal natural logarithmically, and

wherein the controller switches the individual pixels between the first and second states by varying a voltage difference between the first and second electrodes of the first transistor of the photoelectric conversion portion of each pixel.

16. (Original) An image-sensing apparatus as claimed in claim 1,
wherein the controller detects variations in sensitivity of the photoelectric conversion portion of the individual pixels with the photosensitive elements of the individual pixels kept in a dark state.

17. (Original) An image-sensing apparatus comprising:
a plurality of pixels, the pixels each comprising:
a photodiode, having two electrodes, for producing an electric signal in accordance with amount of incident light;
a first MOS transistor having a first electrode connected to one of the electrodes of the photodiode, a second electrode, and a gate electrode;
a second MOS transistor having a first electrode connected to the gate electrode of the first MOS transistor, a second electrode to which a direct-current voltage is applied, and a gate electrode;
a third MOS transistor having a first electrode connected to the gate electrode of the first MOS transistor, a second electrode connected to the first electrode of the first MOS transistor, and a gate electrode; and
a fourth MOS transistor having a first electrode, a second electrode, and a gate electrode connected to the first electrode of the first MOS transistor; and
a controller that detects variations in sensitivity of the individual pixels by feeding a signal to the gate electrode of the second MOS transistor so as to turn on the second MOS transistor and turning off the third MOS transistor so that a predetermined direct-current voltage is applied to the gate electrode of the first MOS transistor and that the gate electrodes of the first and fourth MOS transistors are brought into a cut-off state,
wherein the controller makes the individual pixels perform image sensing by turning off the second MOS transistor and feeding a signal to the gate electrode of the

third MOS transistor so as to turn on the third MOS transistor so that the gate electrodes of the first and fourth MOS transistors are brought into a connected state.

18. (Original) An image-sensing apparatus as claimed in claim 17, wherein, when making the individual pixels perform image sensing, the controller, in a case where the electric signal output from the photodiode is converted natural-logarithmically and is output from the second electrode of the fourth MOS transistor, makes the first MOS transistor operate in a subthreshold region below a threshold value thereof, and, in a case where the electric signal output from the photodiode is converted linearly and is output from the second electrode of the fourth MOS transistor, brings a potential of the second electrode of the first MOS transistor and a potential of the other electrode of the photodiode closer together so as to bring the first MOS transistor into an inactive state and, after allowing the electric signal to be output, performs resetting so that electric charges accumulated at the first and gate electrodes of the first MOS transistor are discharged by switching a level of a voltage applied to the gate electrode of the second MOS transistor so as to bring the second MOS transistor into a conducting state.

19. (Withdrawn) An image-sensing apparatus as claimed in claim 17, wherein the pixels each further comprise a fifth MOS transistor having a first electrode connected to the second electrode of the fourth MOS transistor, a second electrode connected to an output signal line, and a gate electrode connected to a line select line.

20. (Original) An image-sensing apparatus as claimed in claim 17, wherein the pixels each further comprise a sixth MOS transistor, having a first electrode to which a direct-current voltage is applied, a second electrode, and a gate electrode connected to the second electrode of the fourth MOS transistor, for amplifying an output signal output from the second electrode of the fourth transistor.

21. (Withdrawn) An image-sensing apparatus as claimed in claim 19, wherein the pixels each further comprise a capacitor that is connected to a signal line of which one end is connected to the second electrode of the fourth MOS transistor and that is reset through the fourth MOS transistor when a resetting voltage is fed to the first electrode of the fourth MOS transistor.

22. (Withdrawn) An image-sensing apparatus as claimed in claim 19, wherein a direct-current voltage is applied to the first electrode of the fourth MOS transistor, and

wherein the pixels each further comprise:

a seventh MOS transistor having a first electrode connected to the second electrode of the fourth MOS transistor, a second electrode to which a direct-current voltage is applied, and a gate electrode; and

a capacitor that is connected to a signal line of which one end is connected to the second electrode of the fourth MOS transistor and that is reset through the seventh MOS transistor when a resetting voltage is fed to the gate electrode of the seventh MOS transistor.

23. (Original) An image-sensing apparatus as claimed in claim 17, further comprising:

MOS transistors connected by way of output signal lines to the individual pixels so as to serve as load resistors or constant-current sources.

24. (Original) An image-sensing apparatus as claimed in claim 17, wherein the controller detects variations in sensitivity of the individual pixels with the photodiodes of the individual pixels kept in a dark state.

25. (Previously Presented) An image-sensing apparatus comprising:

a plurality of pixels, the pixels each comprising:

a photoelectric conversion portion including a photosensitive element and a field effect transistor configured to produce an electric signal in accordance with an

amount of incident light;

a lead-out path by way of which the electric signal output from the photoelectric conversion portion is fed to an output signal line; and

an integrator circuit that integrates the electric signal output from the photoelectric conversion portion, the integrator circuit including a first transistor to which the electric signal output from the photoelectric conversion portion is fed and a capacitive element connected to the first transistor so that the signal integrated by the integrator circuit is fed by way of the lead-out path to the output signal line; and

a controller that detects a variation in sensitivity of the photoelectric conversion portion of each pixel by causing an electric charge indicative of the threshold voltage of the field effect transistor to accumulate on the field effect transistor and reading out the electric charge via the lead-out path.

26. (Previously Presented) An image-sensing apparatus as claimed in claim 25, wherein the pixels further comprise a second transistor that turns on and off the electric signal output to the output signal line.

27. (Previously Presented) An image-sensing apparatus as claimed in claim 25, wherein the pixels further comprise a third transistor that amplifies the electric signal output from the photoelectric conversion portion.

28. (Previously Presented) An image-sensing apparatus as claimed in claim 25, further comprising a load resistor or a constant-current source connected to the output signal line.

29. (Previously Presented) An image-sensing apparatus as claimed in claim 25, wherein each pixel, when performing image sensing, operates selectively either in a first state in which the photoelectric conversion portion converts the electric signal linearly or in a second state in which the photoelectric conversion portion converts the electric signal natural-logarithmically.

30. (Previously Presented) An image-sensing apparatus comprising:
a plurality of pixels, the pixels each comprising:
a photoelectric conversion portion including:
a photosensitive element for producing an electric signal in accordance with an amount of incident light, the photosensitive element having first and second electrodes to which a direct-current voltage is applied; and
a first transistor having a first electrode connected to the second electrode of the photosensitive element, a second electrode, and a control electrode, the first transistor receiving an output current from the photoelectric element, the first transistor having a plurality of potentials applied to the second electrode; and
a lead-out path by way of which the electric signal output from the photoelectric conversion portion is fed to an output signal line; and
a controller that detects a variation in sensitivity of the photoelectric conversion portion of each pixel by injecting an electric charge into the photoelectric conversion portion.
31. (Previously Presented) An image-sensing apparatus as claimed in claim 30, wherein the pixels further comprise a second transistor that turns on and off the electric signal output to the output signal line.
32. (Previously Presented) An image-sensing apparatus as claimed in claim 30, wherein the pixels further comprise a third transistor that amplifies the electric signal output from the photoelectric conversion portion.
33. (Previously Presented) An image-sensing apparatus as claimed in claim 30, further comprising a load resistor or a constant-current source connected to the output signal line.
34. (Previously Presented) An image-sensing apparatus as claimed in claim 30, wherein each pixel, when performing image sensing, operates selectively either in a first state in which the photoelectric conversion portion converts the electric signal linearly or

in a second state in which the photoelectric conversion portion converts the electric signal natural-logarithmically.

35. (Previously Presented) An image-sensing apparatus comprising:
a plurality of pixels, the pixels each comprising:

a photoelectric conversion portion including:

a photosensitive element for producing an electric signal in accordance with an amount of incident light, the photosensitive element having first and second electrodes to which a direct-current voltage is applied; and

a first transistor having a first electrode connected to the second electrode of the photosensitive element, a second electrode, and a control electrode, the first transistor receiving an output current from the photoelectric element, the first transistor having a plurality of potentials applied to the second electrode;

a lead-out path by way of which the electric signal output from the photoelectric conversion portion is fed to an output signal line; and

an integrator circuit that integrates the electric signal output from the photoelectric conversion portion, the integrator circuit including a first transistor to which the electric signal output from the photoelectric conversion portion is fed and a capacitive element connected to the first transistor so that the signal integrated by the integrator circuit is fed by way of the lead-out path to the output signal line; and

a controller that detects a variation in sensitivity of the photoelectric conversion portion of each pixel by injecting an electric charge into the photoelectric conversion portion.

36. (Previously Presented) An image-sensing apparatus as claimed in claim 35, wherein the pixels further comprise a second transistor that turns on and off the electric signal output to the output signal line.

37. (Previously Presented) An image-sensing apparatus as claimed in claim 35, wherein the pixels further comprise a third transistor that amplifies the electric signal output from the photoelectric conversion portion.

38. (Previously Presented) An image-sensing apparatus as claimed in claim 35, further comprising a load resistor or a constant-current source connected to the output signal line.

39. (Previously Presented) An image-sensing apparatus as claimed in claim 35, wherein each pixel, when performing image sensing, operates selectively either in a first state in which the photoelectric conversion portion converts the electric signal linearly or in a second state in which the photoelectric conversion portion converts the electric signal natural-logarithmically.

40. (New) A method for detecting sensitivity of a photoelectric conversion portion of a pixel within an image-sensing apparatus, the method comprising the steps of:
injecting an electric charge into the photoelectric conversion portion of the pixel;
discharging a portion of the thus injected electric charge for a predetermined period of time; and
detecting an electric charge remaining in the photoelectric conversion portion of the pixel.

41. (New) A method for detecting sensitivity as claimed in claim 40, wherein the step of injecting the electric charge includes changing a voltage applied to the photoelectric conversion portion of the pixel.

42. (New) A method for detecting sensitivity as claimed in claim 40, wherein the steps of injecting the electric charge, discharging a portion of the thus injected electric charge, and detecting an electric charge are repeated for each pixel in the image-sensing apparatus.

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43. (New) A method for detecting sensitivity as claimed in claim 40, wherein the photoelectric conversion portion of the pixel is not exposed to uniform light.

44. (New) A method for detecting sensitivity as claimed in claim 40, wherein the electric charge remaining in the photoelectric conversion portion of the pixel is proportional to a threshold voltage of a transistor within the photoelectric conversion portion of the pixel.